





LOW $V_{CE(SAT)}$ PNP SURFACE MOUNT TRANSISTOR

Features

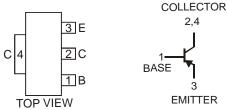
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DXT651)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)







Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage | V_{CBO} | -80 | V |
| Collector-Emitter Voltage | V _{CEO} | -60 | V |
| Emitter-Base Voltage | V _{EBO} | -5 | V |
| Continuous Collector Current | Ic | -3 | А |
| Peak Pulse Collector Current | I _{CM} | -6 | А |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|---|-----------------------------------|-------------|------|
| Power Dissipation (Note 3) @ T _A = 25°C | P _D | 1 | W |
| Thermal Resistance, Junction to Ambient Air (Note 3) @T _A = 25°C | $R_{	hetaJA}$ | 125 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Notes:

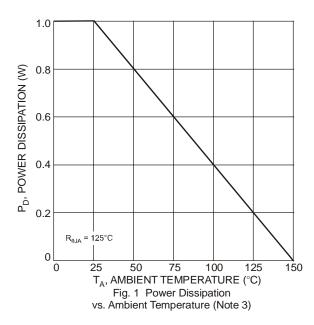
- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

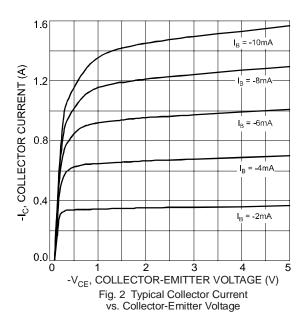


Electrical Characteristics @TA = 25°C unless otherwise specified

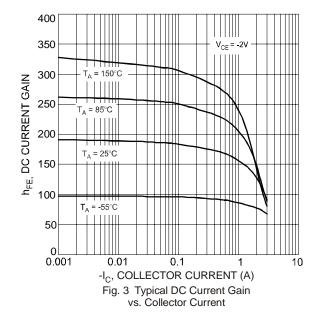
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Conditions |
|--------------------------------------|-------------------------------------|-----------------------|--------------------------|---------------|----------|---|
| OFF CHARACTERISTICS (Note 4) | | | | | | |
| Collector-Base Breakdown Voltage | V _{(BR)CBO} | -80 | _ | _ | V | $I_C = -100\mu A, I_E = 0$ |
| Collector-Emitter Breakdown Voltage | V _{(BR)CEO} | -60 | _ | _ | V | $I_C = -10 \text{mA}, I_B = 0$ |
| Emitter-Base Breakdown Voltage | V _{(BR)EBO} | -5 | _ | _ | V | $I_E = -100 \mu A, I_C = 0$ |
| Collector Cutoff Current | I _{CBO} | _ | _ | -0.1 -10 | μA μA | V _{CB} = -60V, I _E = 0 V _{CB} = -60V, I _E = 0, T _A = 100°C |
| Emitter Cutoff Current | I _{EBO} | | _ | -0.1 | μΑ | $V_{EB} = -4V, I_C = 0$ |
| ON CHARACTERISTICS (Note 4) | | | | | | |
| Collector-Emitter Saturation Voltage | V _{CE(SAT)} | | -0.08 -0.2 | -0.3 -0.6 | ٧ | $I_C = -1A$, $I_B = -100mA$ $I_C = -3A$, $I_B = -300mA$ |
| Base-Emitter Saturation Voltage | V _{BE(SAT)} | _ | -0.9 | -1.25 | V | I _C = -1A, I _B = -100mA |
| Base-Emitter Turn-On Voltage | V _{BE(ON)} | | -0.8 | -1 | V | $V_{CE} = -2V, I_{C} = -1A$ |
| DC Current Gain | h _{FE} | 70 100 80 40 | 200 180 160 140 | 300 — — | | V _{CE} = -2V, I _C = -50mA V _{CE} = -2V, I _C = -500mA V _{CE} = -2V, I _C = -1A V _{CE} = -2V, I _C = -2A |
| AC CHARACTERISTICS | | | | | | |
| Transition Frequency | f⊤ | 100 | 145 | _ | MHz | $V_{CE} = -10V$, $I_{C} = -50mA$, $f = 100MHz$ |
| Output Capacitance | C _{obo} | | _ | 30 | рF | $V_{CB} = -10V$, $f = 1MHz$ |
| Switching Times | t _{on} t _{off} | | 45 200 | _ | ns ns | $I_{C} = -500 \text{mA}, V_{CC} = -10 \text{V}$ $I_{B1} = I_{B2} = -50 \text{mA}$ |

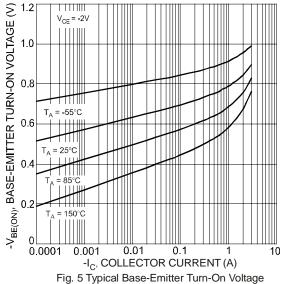
Notes: 4. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.

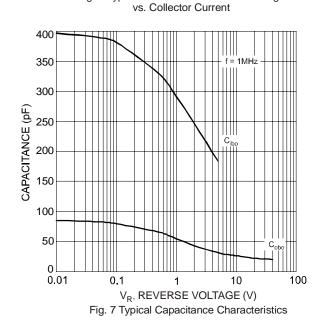












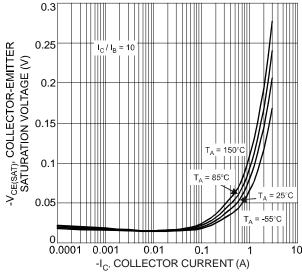


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

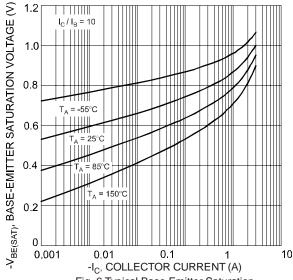


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

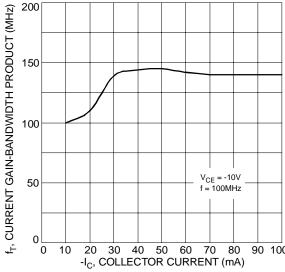


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

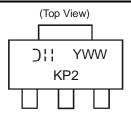


Ordering Information (Note 5)

| Device | Packaging | Shipping |
|-----------|-----------|------------------|
| DXT751-13 | SOT89-3L | 2500/Tape & Reel |

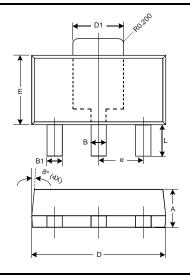
5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

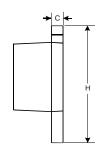
Marking Information



KP2 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

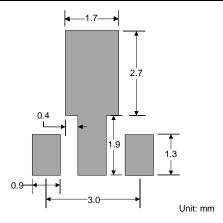
Package Outline Dimensions





| SOT89-3L | | | | | |
|----------------------|------|------|------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 1.40 | 1.60 | 1.50 | | |
| В | 0.45 | 0.55 | 0.50 | | |
| B1 | 0.37 | 0.47 | 0.42 | | |
| С | 0.35 | 0.43 | 0.38 | | |
| D | 4.40 | 4.60 | 4.50 | | |
| D1 | 1.50 | 1.70 | 1.60 | | |
| Е | 2.40 | 2.60 | 2.50 | | |
| е | _ | _ | 1.50 | | |
| Н | 3.95 | 4.25 | 4.10 | | |
| L | 0.90 | 1.20 | 1.05 | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout



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>>Diodes Incorporated(达迩科技(美台))